

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

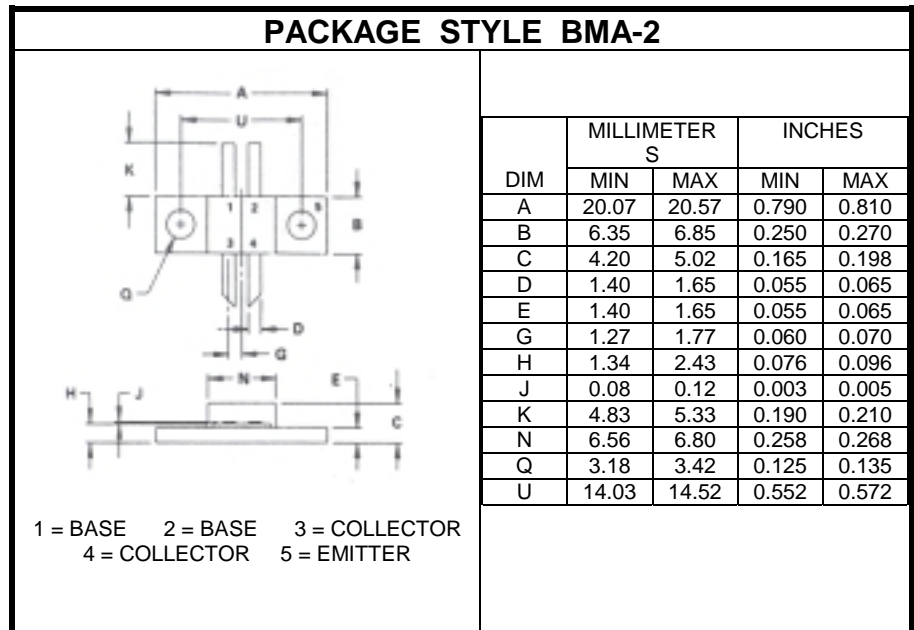
The **TPV5051** is Designed for AB Push Pull, Common Emitter from 470 to 860 MHz Applications.

FEATURES:

- Gold Metalization
- Diffused Ballast Resistor

MAXIMUM RATINGS

I_C	9.0 A
V_{CEO}	30 V
V_{CBO}	45 V
P_{DISS}	97 W @ $T_C = 25\text{ }^\circ\text{C}$
T_J	-65 $^\circ\text{C}$ to +200 $^\circ\text{C}$
T_{STG}	-65 $^\circ\text{C}$ to +150 $^\circ\text{C}$
θ_{JC}	1.8 $^\circ\text{C/W}$


CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 60\text{ mA}$	30			V
BV_{CBO}	$I_C = 20\text{ mA}$	45			V
BV_{EBO}	$I_E = 6.0\text{ mA}$	4.0			V
BV_{CER}	$I_C = 10\text{ mA}$ $R_{BE} = 50\ \Omega$	40			V
I_{CEO}	$V_{CE} = 28\text{ V}$			10	mA
h_{FE}	$V_{CE} = 20\text{ V}$ $I_C = 800\text{ mA}$	10			---
C_{ob}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz (EACH SIDE)}$			40	pF
P_G	$V_{CE} = 28\text{ V}$ $P_{out} = 50\text{ W}$ $I_q = 2X50\text{ mA}$	6.5			dB
η_C	$f = 860\text{ MHz}$	45			%